

650V 25A Field Stop Trench IGBT

V _{CES}	650V
I _{C(100°C)}	25A
V _{CE(sat) (Typ.)}	1.6V
P _D	174W

Features

- 1) Low Collector Emitter Saturation Voltage
- 2) High Speed Switching
- 3) Low Switching Loss & Soft Switching
- 4) Built in Very Fast & Soft Recovery FRD (RFN - Series)
- 5) Pb free Lead Plating ; RoHS Compliant

Applications

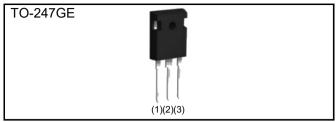
PFC

UPS

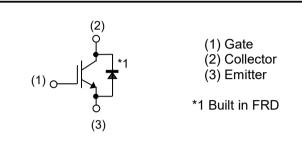
Power Conditioner

IH

Outline



Inner Circuit



Packaging Specifications

	Packaging	Tube
	Reel Size (mm)	-
Type	Tape Width (mm)	-
Туре	Basic Ordering Unit (pcs)	600
	Packing code	C13
	Marking	RGTH50TS65D

•Absolute Maximum Ratings (at T_c = 25°C unless otherwise specified)

			,	
Parameter		Symbol	Value	Unit
Collector - Emitter Voltage		V _{CES}	650	V
Gate - Emitter Voltage		V _{GES}	±30	V
Collector Current	$T_{\rm C} = 25^{\circ}{\rm C}$	۱ _C	50	А
Collector Current	T _C = 100°C	۱ _C	25	А
Pulsed Collector Current		I _{CP} *1	100	А
Diode Forward Current	$T_{\rm C} = 25^{\circ}{\rm C}$	I _F	35	А
Diode Forward Current	T _C = 100°C	I _F	20	А
Diode Pulsed Forward Current		I _{FP} ^{*1}	100	А
Dower Dissinction	$T_{C} = 25^{\circ}C$	P _D	174	W
Power Dissipation	T _C = 100°C	P _D	87	W
Operating Junction Temperature		Tj	-40 to +175	°C
Storage Temperature		T _{stg}	-55 to +175	°C
*1 Dules width limited by T				

*1 Pulse width limited by T_{jmax.}

RGTH50TS65DGC13

•Thermal Resistance

Parameter	Symbol	Values			Unit
	Symbol	Min.	Тур.	Max.	Unit
Thermal Resistance IGBT Junction - Case	$R_{\theta(j\text{-}c)}$	-	-	0.86	°C/W
Thermal Resistance Diode Junction - Case	$R_{\theta(j\text{-}c)}$	-	-	2.28	°C/W

●IGBT Electrical Characteristics (at T_j = 25°C unless otherwise specified)

Parameter	Symbol	Conditions	Values			Unit	
Faranielei	er Symbol Conditions –		Min.	Тур.	Max.	Unit	
Collector - Emitter Breakdown Voltage	BV _{CES}	I _C = 10μΑ, V _{GE} = 0V	650	-	-	V	
Collector Cut - off Current	I _{CES}	V _{CE} = 650V, V _{GE} = 0V	-	-	10	μA	
Gate - Emitter Leakage Current	I _{GES}	V _{GE} = ±30V, V _{CE} = 0V	-	-	±200	nA	
Gate - Emitter Threshold Voltage	$V_{GE(th)}$	V _{CE} = 5V, I _C = 17.5mA	4.5	5.5	6.5	V	
Collector - Emitter Saturation Voltage	V _{CE(sat)}	I _C = 25A, V _{GE} = 15V T _j = 25°C T _j = 175°C	-	1.6 2.1	2.1 -	V	

●IGBT Electrical Characteristics (at T_j = 25°C unless otherwise specified)

				Values		
Parameter	Symbol	Conditions	Min.	Тур.	Max.	Unit
Input Capacitance	C _{ies}	V _{CE} = 30V	-	1410	-	
Output Capacitance	C _{oes}	V _{GE} = 0V	-	57	-	pF
Reverse Transfer Capacitance	C _{res}	f = 1MHz	-	22	-	
Total Gate Charge	Q_g	V _{CE} = 300V	-	49	-	
Gate - Emitter Charge	Q_{ge}	I _C = 25A	-	15	-	nC
Gate - Collector Charge	Q_{gc}	V _{GE} = 15V	-	19	-	
Turn - on Delay Time	t _{d(on)}	I _C = 25A, V _{CC} = 400V	-	27	-	
Rise Time	t _r	V _{GE} = 15V, R _G = 10Ω	-	38	-	20
Turn - off Delay Time	$t_{d(off)}$	T _j = 25°C	-	94	-	ns
Fall Time	t _f	Inductive Load	-	50	-	
Turn - on Delay Time	t _{d(on)}	I _C = 25A, V _{CC} = 400V	-	27	-	
Rise Time	t _r	V _{GE} = 15V, R _G = 10Ω	-	38	-	nc
Turn - off Delay Time	$t_{d(off)}$	T _j = 175°C	-	107	-	ns
Fall Time	t _f	Inductive Load	-	65	-	
		I _C = 100A, V _{CC} = 520V				
Reverse Bias Safe Operating Area	RBSOA	V _P = 650V, V _{GE} = 15V	FU	LL SQUA	RE	-
		R _G = 60Ω, T _j = 175°C				

•FRD Electrical Characteristics (at $T_j = 25^{\circ}C$ unless otherwise specified)

Deremeter	Symbol	Conditions	Values			Unit	
Parameter	Symbol	Conditions	Min.	Тур.	Max.	Unit	
Diode Forward Voltage	V _F	I _F = 20A T _j = 25°C T _j = 175°C	-	1.45 1.25	1.9 -	v	
Diode Reverse Recovery Time	t _{rr}	I _F = 20A	-	58	-	ns	
Diode Peak Reverse Recovery Current	I _{rr}	V _{CC} = 400V di _F /dt = 200A/µs	-	6.3	-	А	
Diode Reverse Recovery Charge	Q _{rr}	T _j = 25°C	-	0.20	-	μC	
Diode Reverse Recovery Time	t _{rr}	I _F = 20A	-	256	-	ns	
Diode Peak Reverse Recovery Current	I _{rr}	V _{CC} = 400V di _F /dt = 200A/µs	-	10.4	-	А	
Diode Reverse Recovery Charge	Q _{rr}	T _j = 175°C	-	1.35	-	μC	

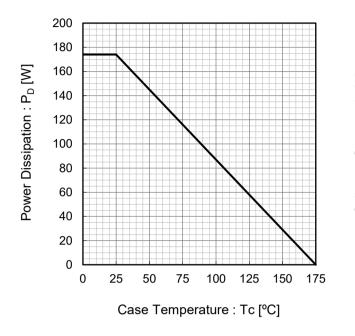


Fig.1 Power Dissipation vs. Case Temperature

Fig.2 Collector Current vs. Case Temperature

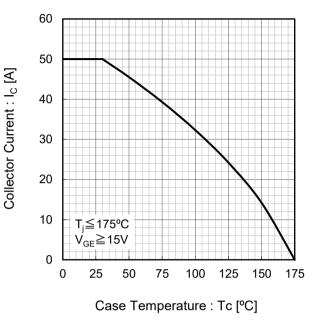
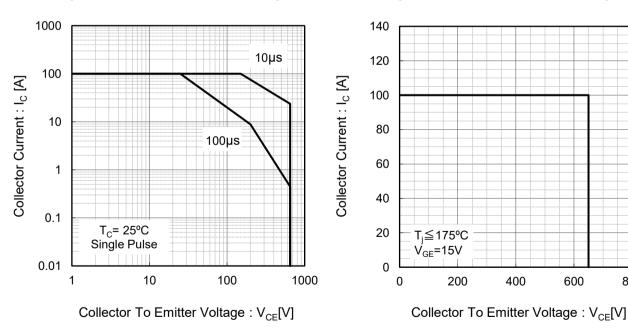


Fig.3 Forward Bias Safe Operating Area

Fig.4 Reverse Bias Safe Operating Area



800

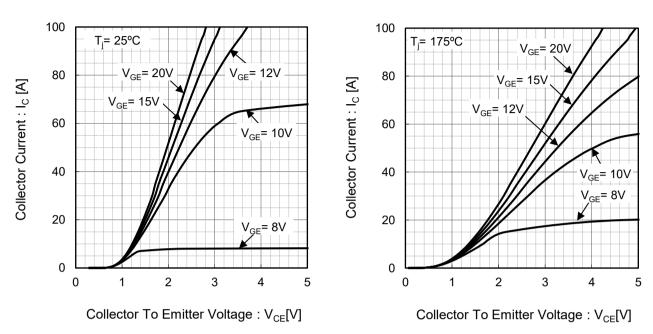


Fig.5 Typical Output Characteristics

Fig.7 Typical Transfer Characteristics

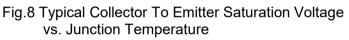
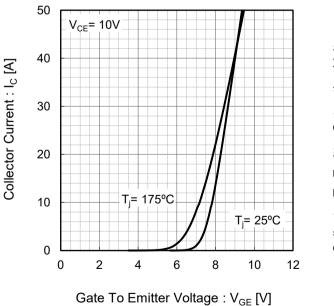


Fig.6 Typical Output Characteristics



4 V_{GE}= 15V Collector To Emitter Saturation Voltage I_C= 50A 3 : V_{CE(sat)} [V] I_C= 25A 2 I_C= 12A 1 0 25 50 75 100 125 150 175 Junction Temperature : T_i [°C]

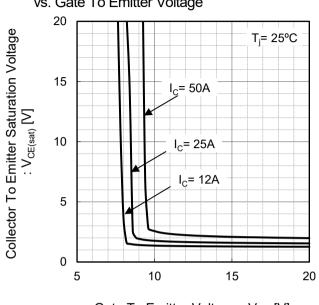
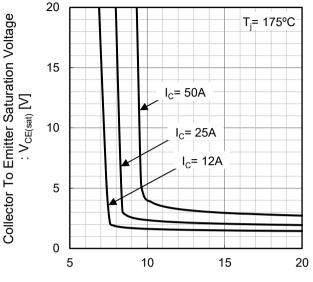


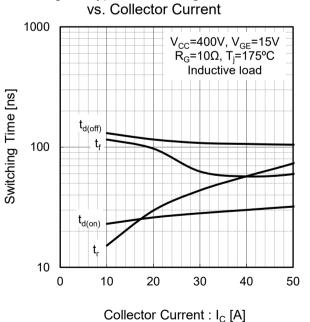
Fig.9 Typical Collector To Emitter Saturation Voltage vs. Gate To Emitter Voltage





Gate To Emitter Voltage : V_{GE} [V]

Gate To Emitter Voltage : V_{GE} [V]



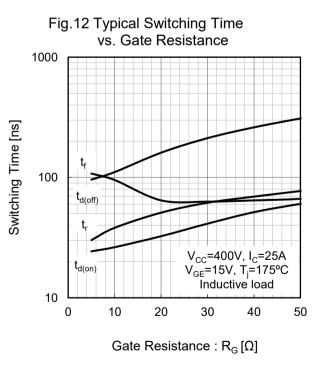
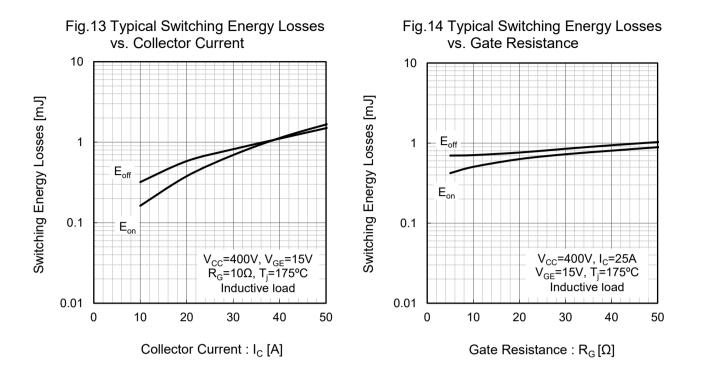
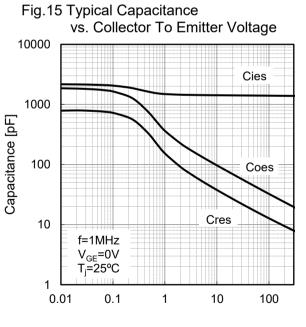


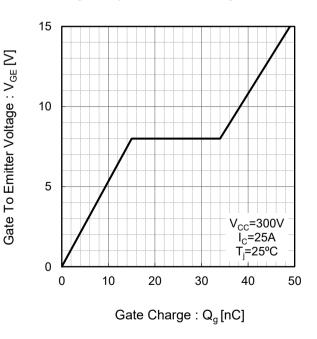
Fig.11 Typical Switching Time





Collector To Emitter Voltage : $V_{CE}[V]$

Fig.16 Typical Gate Charge



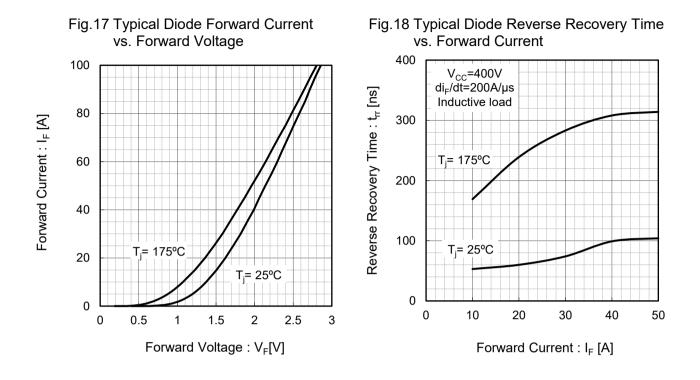


Fig.19 Typical Diode Reverse Recovery Current vs. Forward Current

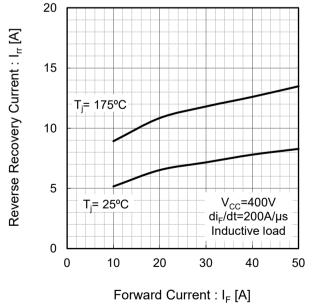
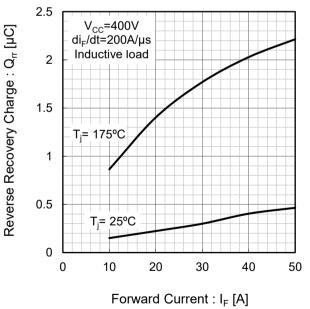


Fig.20 Typical Diode Reverse Recovery Charge vs. Forward Current



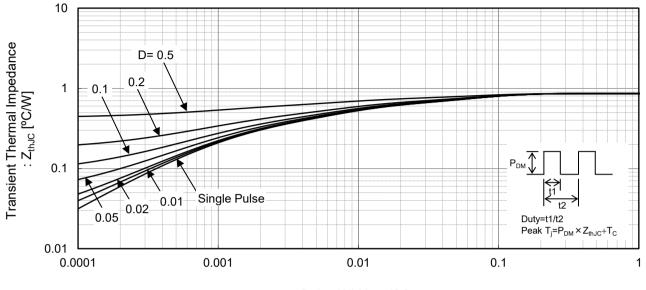
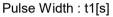


Fig.21 IGBT Transient Thermal Impedance



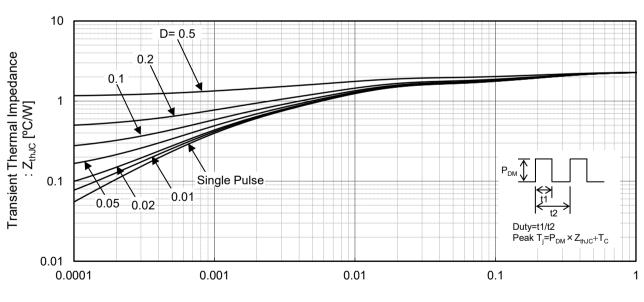


Fig.22 Diode Transient Thermal Impedance

Pulse Width : t1[s]

●Inductive Load Switching Circuit and Waveform

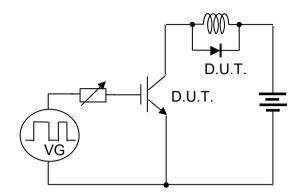


Fig.23 Inductive Load Circuit

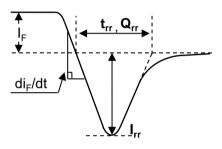


Fig.25 Diode Reverce Recovery Waveform

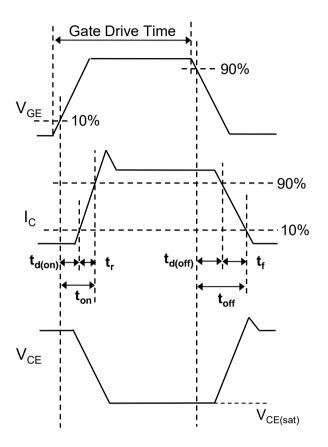


Fig.24 Inductive Load Waveform



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